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Kind regards,

Team Nexperia



PMV35EPE

30 V, P-channel Trench MOSFET

6 July 2016

Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

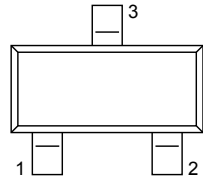
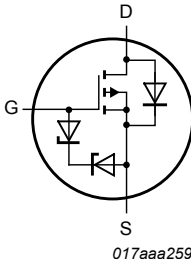
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j = 25\text{ °C}$	-	-	-30	V
V_{GS}	gate-source voltage		-20	-	20	V
I_D	drain current	$V_{GS} = -10\text{ V}; T_{amb} = 25\text{ °C}; t \leq 5\text{ s}$	[1]	-	-5.3	A
Static characteristics						
R_{DSon}	drain-source on-state resistance	$V_{GS} = -10\text{ V}; I_D = -4.2\text{ A}; T_j = 25\text{ °C}$	-	35	45	mΩ

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 <p>TO-236AB (SOT23)</p>	 <p>017aaa259</p>
2	S	source		
3	D	drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
PMV35EPE	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

7. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PMV35EPE	EK%

[1] % = placeholder for manufacturing site code

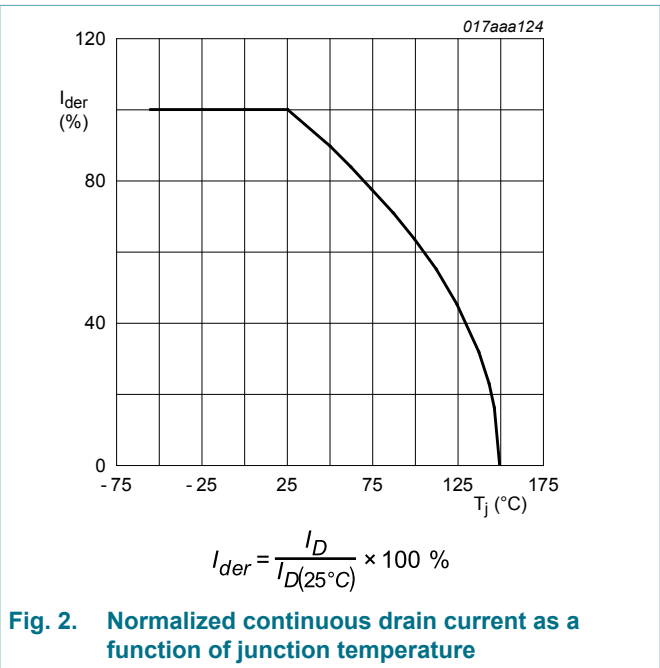
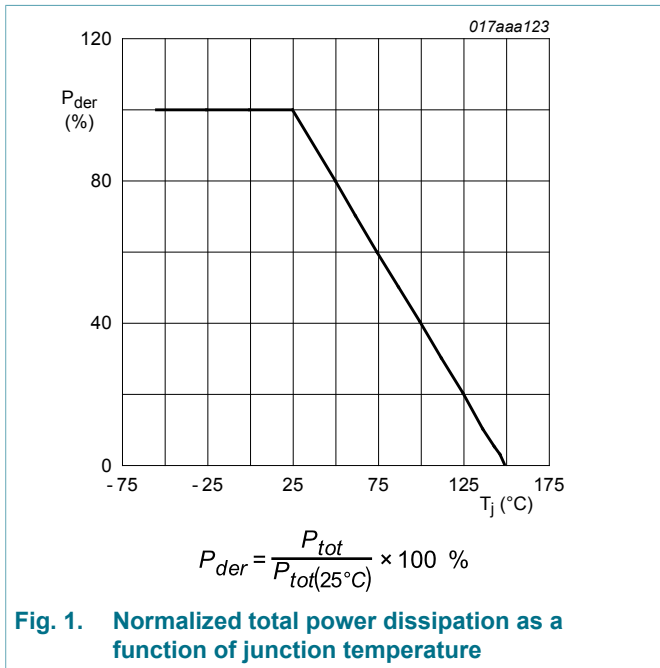
8. Limiting values

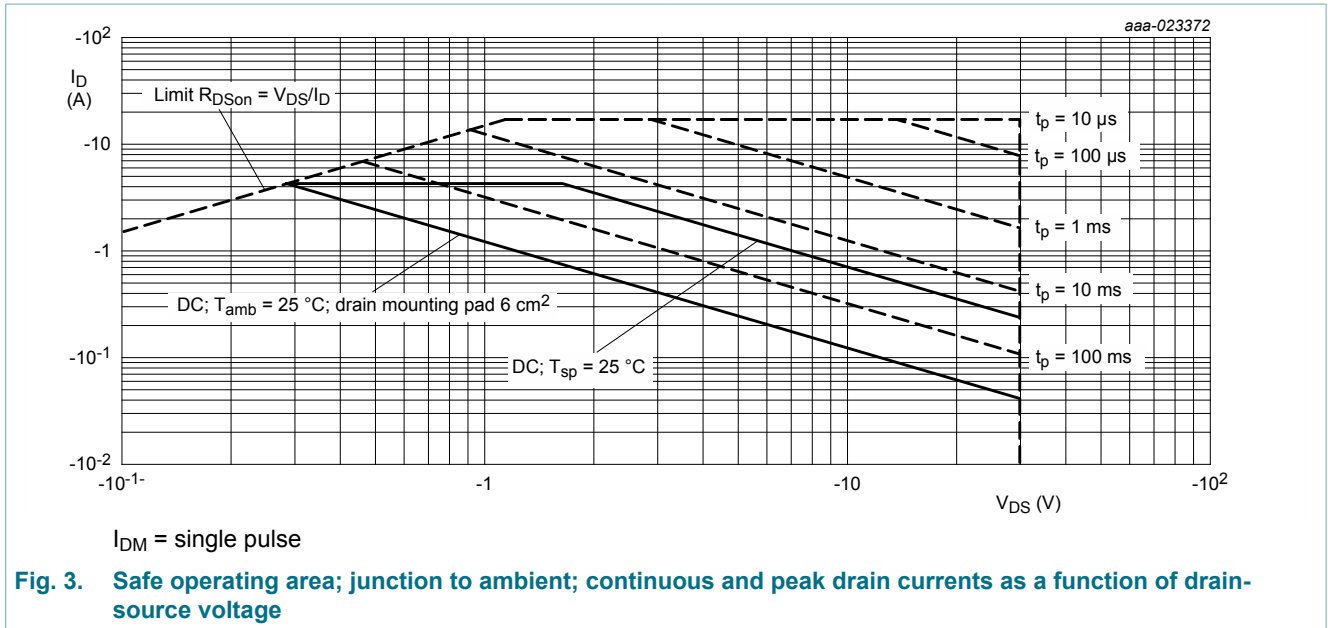
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	-30	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = -10 V; T _{amb} = 25 °C; t ≤ 5 s	[1]	-	-5.3	A
		V _{GS} = -10 V; T _{amb} = 25 °C	[1]	-	-4.2	A
		V _{GS} = -10 V; T _{amb} = 100 °C	[1]	-	-2.7	A
I _{DM}	peak drain current	T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs		-	-17	A
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	480	mW
			[1]	-	1.2	W
		T _{sp} = 25 °C		-	6.95	W
T _j	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-drain diode						
I _S	source current	T _{amb} = 25 °C	[1]	-	-4	A

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.





9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	227	261	K/W
			[2]	-	91	104	K/W
		$t \leq 5 \text{ s}$	[2]	-	57	66	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	13	18	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm^2 .

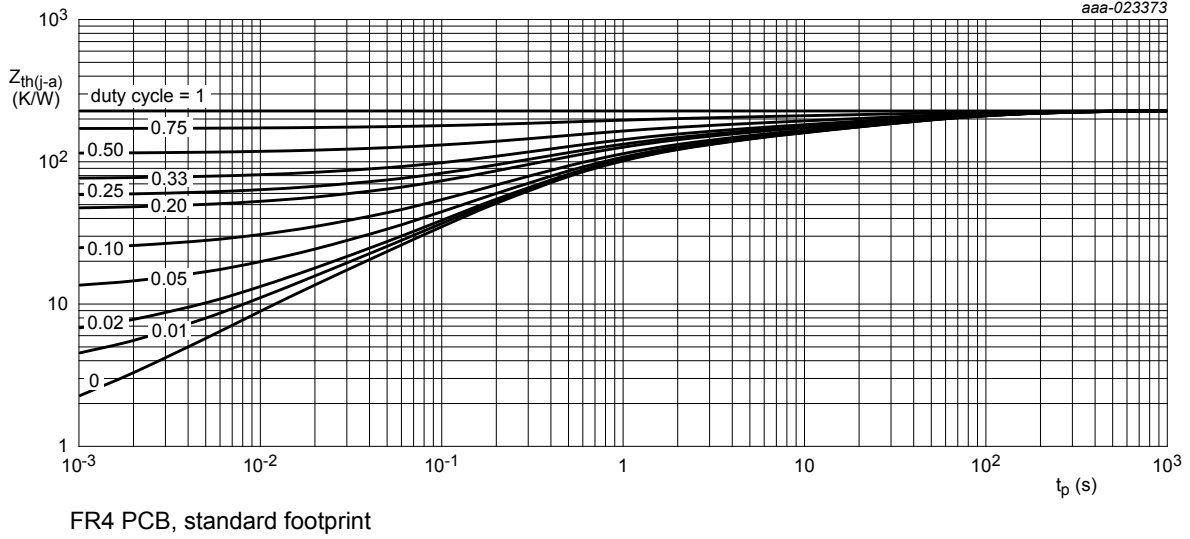


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

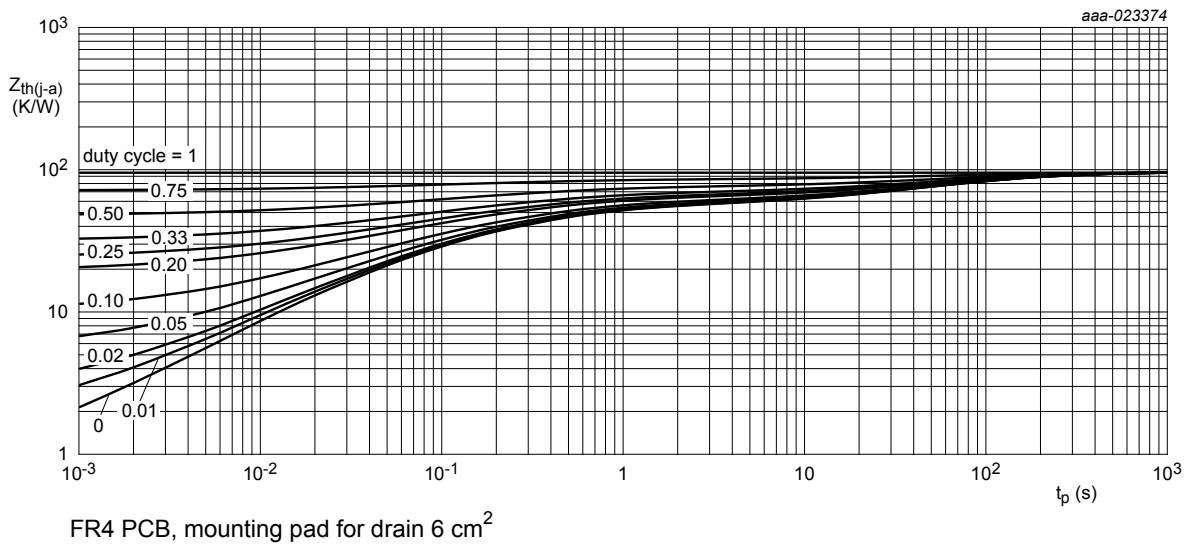


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-30	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = -250 \mu A; V_{DS}=V_{GS}; T_j = 25 \text{ }^\circ C$	-1	-2	-3	V
I_{DSS}	drain leakage current	$V_{DS} = -30 V; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-1	μA
I_{GSS}	gate leakage current	$V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	10	μA
		$V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-10	μA
		$V_{GS} = 10 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	2	μA
		$V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-	-2	μA
R_{DSon}	drain-source on-state resistance	$V_{GS} = -10 V; I_D = -4.2 A; T_j = 25 \text{ }^\circ C$	-	35	45	m Ω
		$V_{GS} = -10 V; I_D = -4.2 A; T_j = 150 \text{ }^\circ C$	-	51	67	m Ω
		$V_{GS} = -4.5 V; I_D = -3.3 A; T_j = 25 \text{ }^\circ C$	-	49	72	m Ω
g_{fs}	forward transconductance	$V_{DS} = -10 V; I_D = -4.2 A; T_j = 25 \text{ }^\circ C$	-	13.5	-	S
R_G	gate resistance	$f = 1 \text{ MHz}$	-	13	-	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$V_{DS} = -15 V; I_D = -4.2 A; V_{GS} = -10 V; T_j = 25 \text{ }^\circ C$	-	12.8	19.2	nC
Q_{GS}	gate-source charge		-	2.2	-	nC
Q_{GD}	gate-drain charge		-	2.2	-	nC
C_{iss}	input capacitance	$V_{DS} = -15 V; f = 1 \text{ MHz}; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	793	-	pF
C_{oss}	output capacitance		-	134	-	pF
C_{rss}	reverse transfer capacitance		-	84	-	pF
$t_{d(on)}$	turn-on delay time		-	6	-	ns
t_r	rise time	$R_{G(ext)} = 6 \text{ } \Omega; T_j = 25 \text{ }^\circ C$	-	19	-	ns
$t_{d(off)}$	turn-off delay time		-	36	-	ns
t_f	fall time		-	19	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = -4 A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$	-	-0.8	-1.2	V

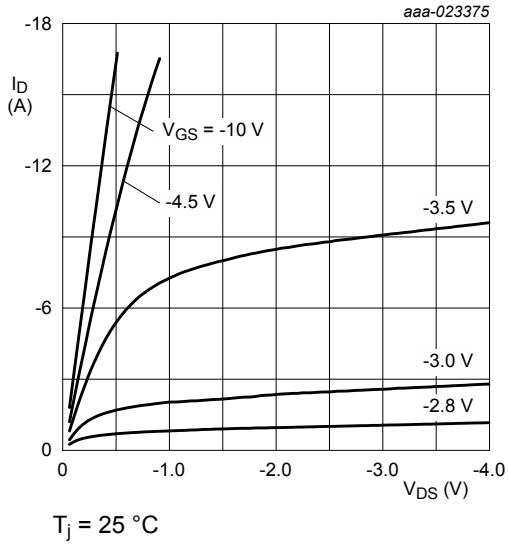


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

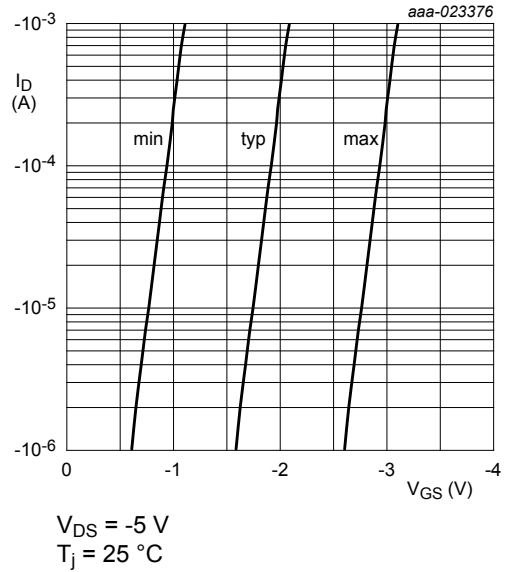


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

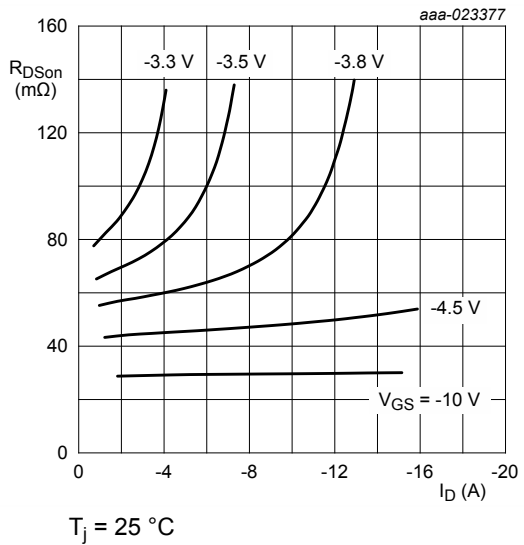


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

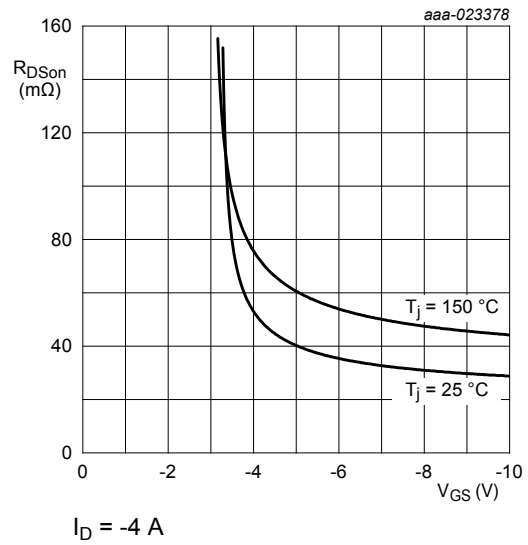
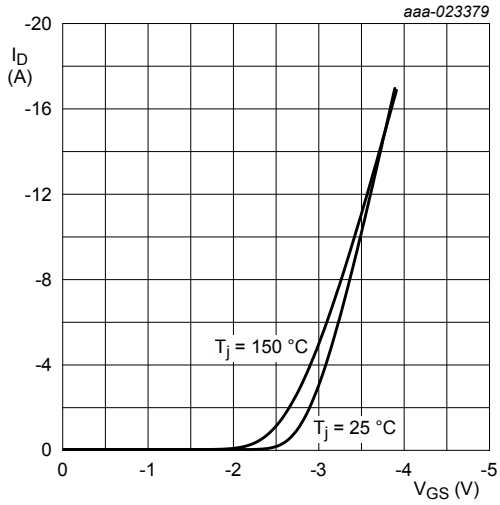
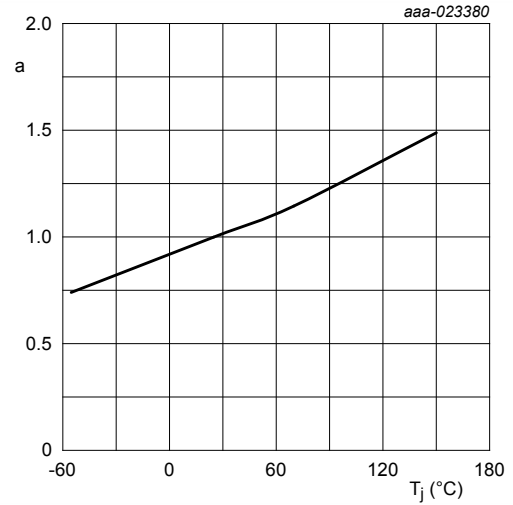


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



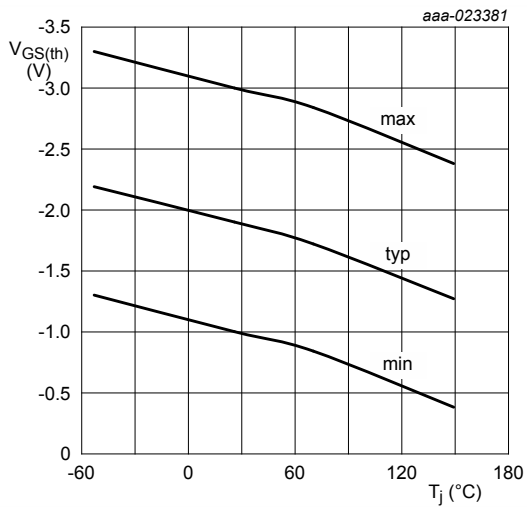
$$V_{DS} > I_D \times R_{DSon}$$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



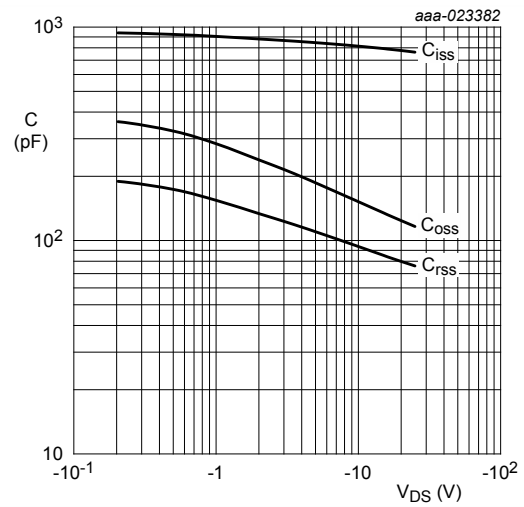
$$a = \frac{R_{DSon}}{R_{DSon}(25^\circ\text{C})}$$

Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



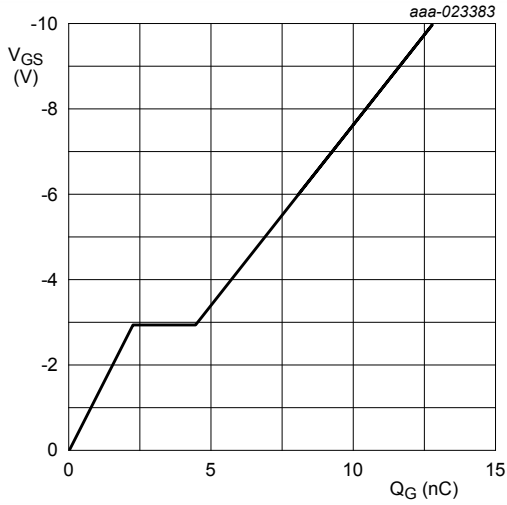
$$I_D = -250 \mu\text{A}; V_{DS} = V_{GS}$$

Fig. 12. Gate-source threshold voltage as a function of junction temperature



$$f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$$

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{DS} = -15\text{ V}; I_D = -4\text{ A}$

Fig. 14. Gate-source voltage as a function of gate charge; typical values

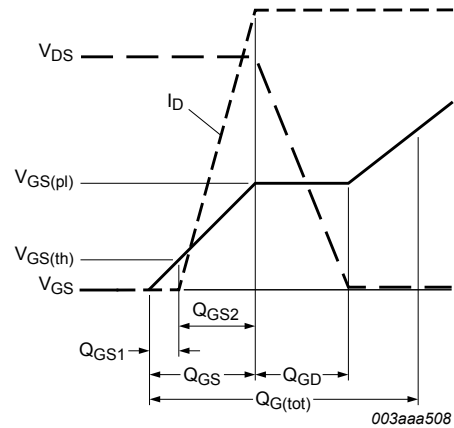
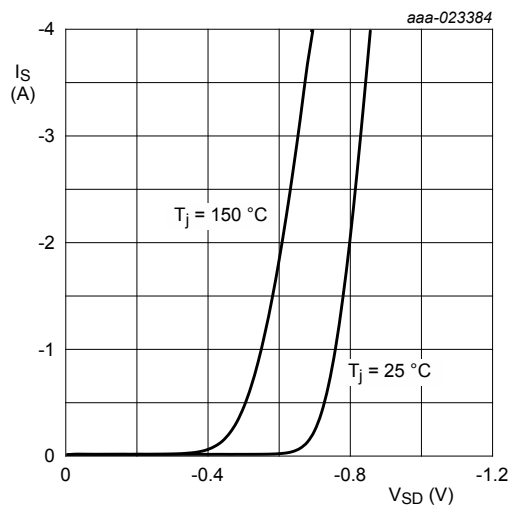


Fig. 15. Gate charge waveform definitions



$V_{GS} = 0\text{ V}$

Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

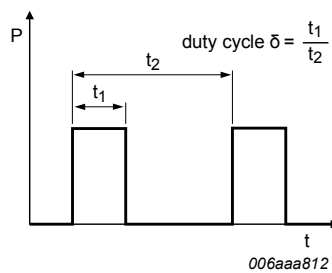
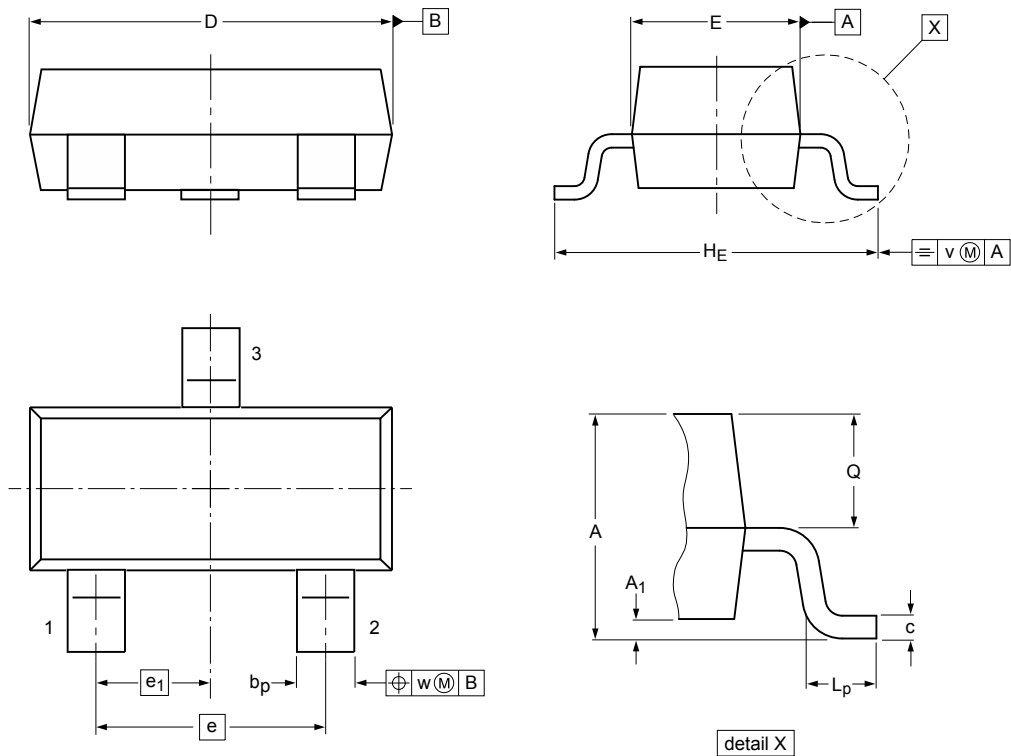


Fig. 17. Duty cycle definition

12. Package outline

Plastic surface-mounted package; 3 leads

SOT23



Dimensions (mm are the original dimensions)

Unit	A	A ₁	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
max	1.1	0.1	0.48	0.15	3.0	1.4			2.5	0.45	0.55		
nom							1.9	0.95				0.2	0.1
min	0.9		0.38	0.09	2.8	1.2			2.1	0.15	0.45		

sot023_po

Outline version	References			European projection	Issue date
	IEC	JEDEC	JEITA		
SOT23		TO-236AB			14-06-19 14-09-22

Fig. 18. Package outline TO-236AB (SOT23)

13. Soldering

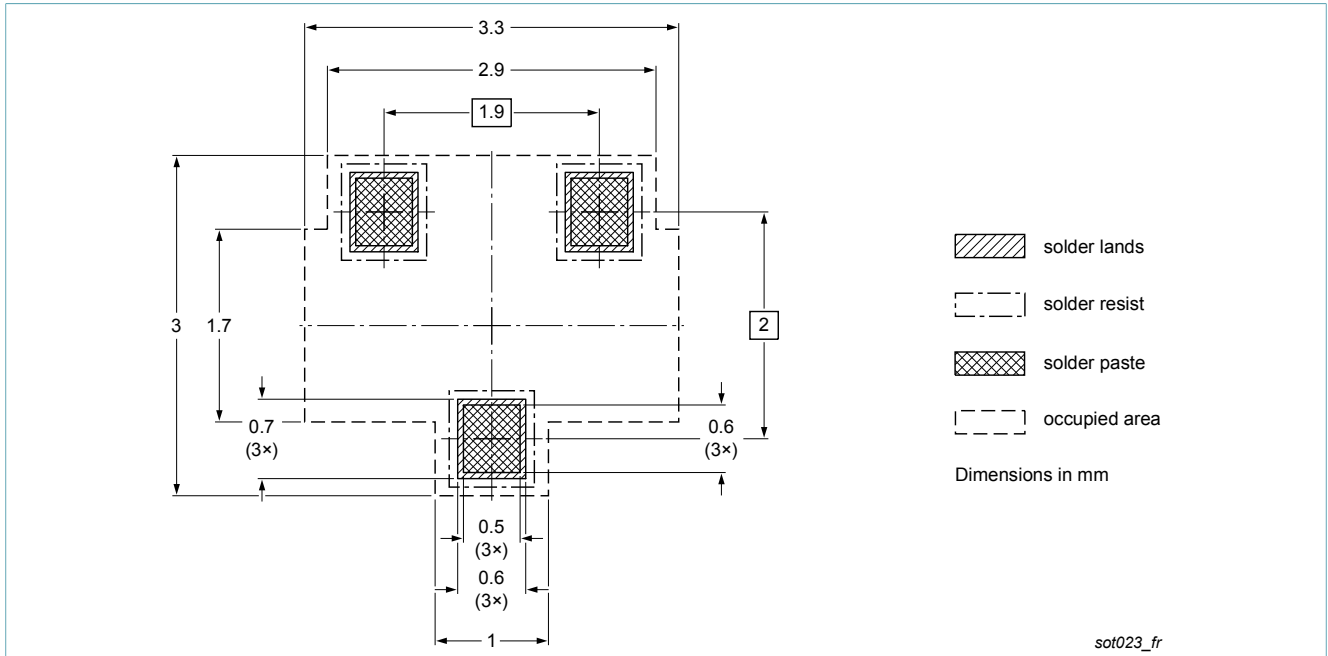


Fig. 19. Reflow soldering footprint for TO-236AB (SOT23)

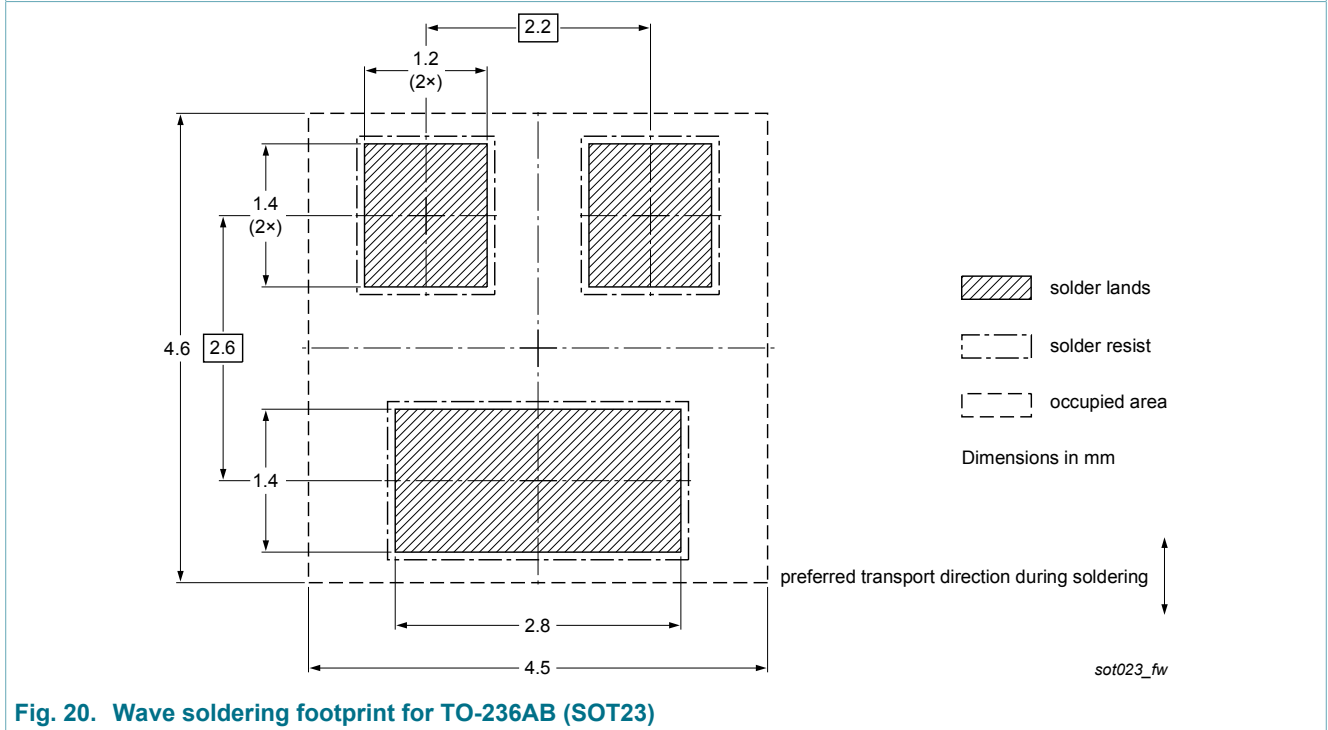


Fig. 20. Wave soldering footprint for TO-236AB (SOT23)

14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV35EPE v.1	20160706	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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